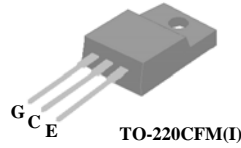


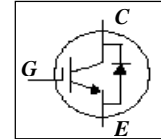


Features

- ▼ High Speed Switching
- ▼ Low Saturation Voltage
 $V_{CE(sat),typ.}=1.7V @ I_C=12A$
- ▼ RoHS Compliant Product



| | |
|-----------|------|
| V_{CES} | 600V |
| I_C | 12A |



Absolute Maximum Ratings

| Symbol | Parameter | Rating | Units |
|-------------------------|---------------------------------------|------------|------------|
| V_{CES} | Collector-Emitter Voltage | 600 | V |
| V_{GE} | Gate-Emitter Voltage | ± 20 | V |
| $I_C @ T_C=25^\circ C$ | Collector Current | 25 | A |
| $I_C @ T_C=100^\circ C$ | Collector Current | 12 | A |
| I_{CM} | Pulsed Collector Current ¹ | 50 | A |
| $I_F @ T_C=100^\circ C$ | Diode Forward Current | 8 | A |
| I_{FM} | Diode Pulse Forward Current | 40 | A |
| $P_D @ T_C=25^\circ C$ | Maximum Power Dissipation | 33 | W |
| T_{STG} | Storage Temperature Range | -55 to 150 | $^\circ C$ |
| T_J | Operating Junction Temperature Range | 150 | $^\circ C$ |

Notes:

1. Pulse width limited by Max. junction temperature .

Thermal Data

| Symbol | Parameter | Value | Units |
|---------------|-------------------------------------|-------|--------------|
| Rthj-c | Thermal Resistance Junction-Case | 3.8 | $^\circ C/W$ |
| Rthj-c(Diode) | Thermal Resistance Junction-Case | 5 | $^\circ C/W$ |
| Rthj-a | Thermal Resistance Junction-Ambient | 65 | $^\circ C/W$ |

Electrical Characteristics @ $T_J=25^\circ C$ (unless otherwise specified)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|---------------|--------------------------------------|----------------------------------|------|------|-----------|-------|
| I_{GES} | Gate-to-Emitter Leakage Current | $V_{GE}=\pm 20V, V_{CE}=0V$ | - | - | ± 100 | nA |
| I_{CES} | Collector-Emitter Leakage Current | $V_{CE}=600V, V_{GE}=0V$ | - | - | 1 | mA |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $V_{GE}=15V, I_C=12A$ | - | 1.7 | 2.2 | V |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $V_{GE}=15V, I_C=25A$ | - | 1.9 | - | V |
| $V_{GE(th)}$ | Gate Threshold Voltage | $V_{CE}=V_{GE}, I_C=250\mu A$ | 2 | - | 6 | V |
| Q_g | Total Gate Charge | $I_C=20A$ | - | 95 | 150 | nC |
| Q_{ge} | Gate-Emitter Charge | $V_{CC}=480V$ | - | 16 | - | nC |
| Q_{gc} | Gate-Collector Charge | $V_{GE}=15V$ | - | 35 | - | nC |
| $t_{d(on)}$ | Turn-on Delay Time | $V_{CE}=480V,$ | - | 40 | - | ns |
| t_r | Rise Time | $I_C=20A,$ | - | 20 | - | ns |
| $t_{d(off)}$ | Turn-off Delay Time | $V_{GE}=15V,$ | - | 140 | - | ns |
| t_f | Fall Time | $R_G=5\Omega,$ Inductive Load | - | 200 | 400 | ns |
| E_{on} | Turn-On Switching Loss | | - | 0.1 | - | mJ |
| E_{off} | Turn-Off Switching Loss | | - | 1 | - | mJ |
| C_{ies} | Input Capacitance | $V_{GE}=0V$ | - | 2760 | 4400 | pF |
| C_{oes} | Output Capacitance | $V_{CE}=30V$ | - | 65 | - | pF |
| C_{res} | Reverse Transfer Capacitance | $f=1.0MHz$ | - | 40 | - | pF |
| V_F | FRD Forward Voltage | $I_F=8A$ | - | 1.8 | 2.4 | V |
| t_{rr} | FRD Reverse Recovery Time | $I_F=8A$ | - | 30 | - | ns |
| Q_{rr} | FRD Reverse Recovery Charge | $di/dt = 100 A/\mu s$ | - | 30 | - | nC |

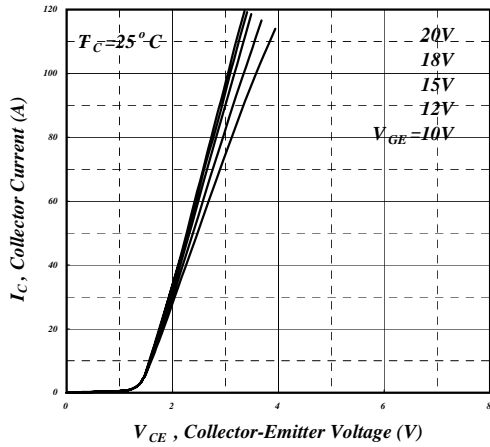


Fig 1. Typical Output Characteristics

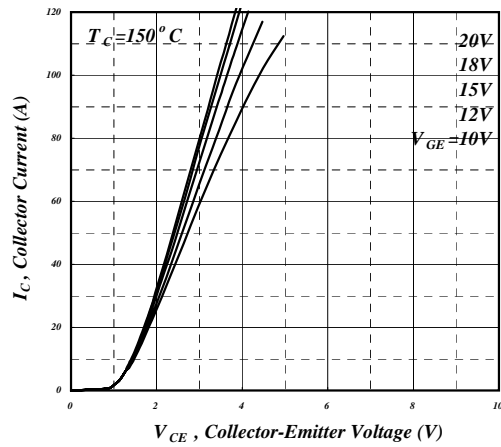


Fig 2. Typical Output Characteristics

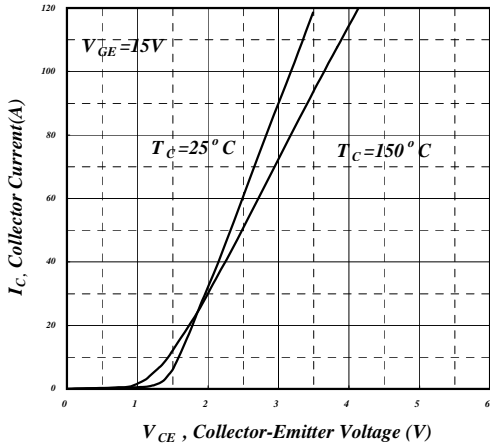


Fig 3. Typical Saturation Voltage Characteristics

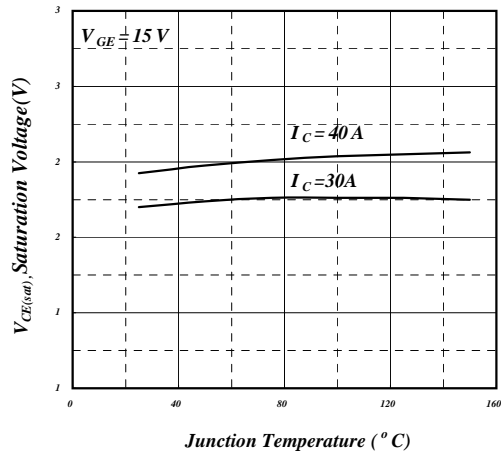


Fig 4. Typical Collector- Emitter Voltage v.s. Junction Temperature

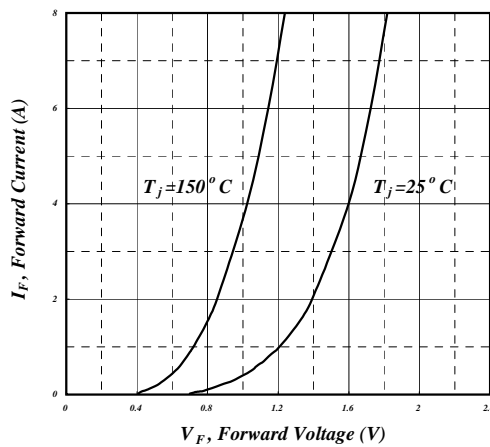


Fig 5. Forward Characteristic of Diode

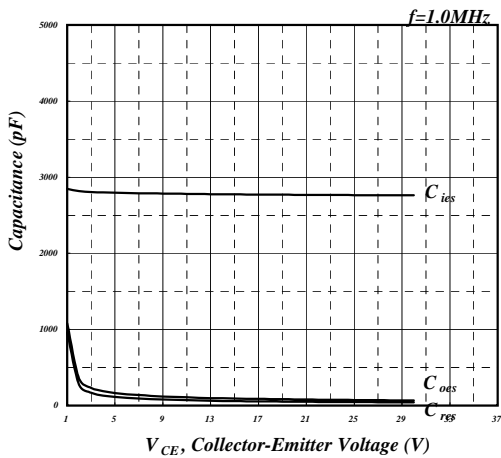


Fig 6. Typical Capacitance Characteristics

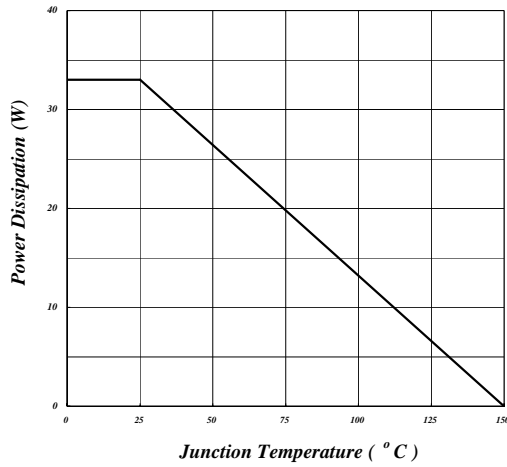


Fig7. Power Dissipation vs. Junction Temperature

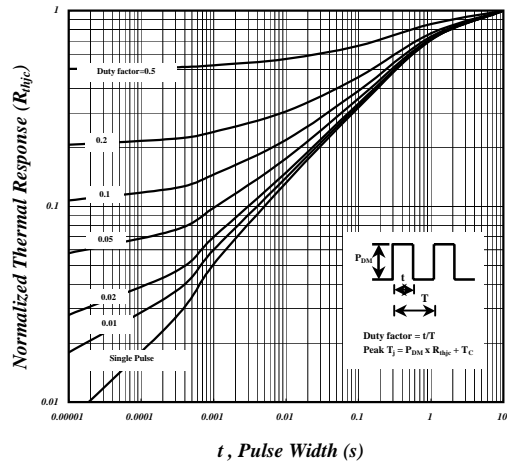


Fig 8. Effective Transient Thermal Impedance

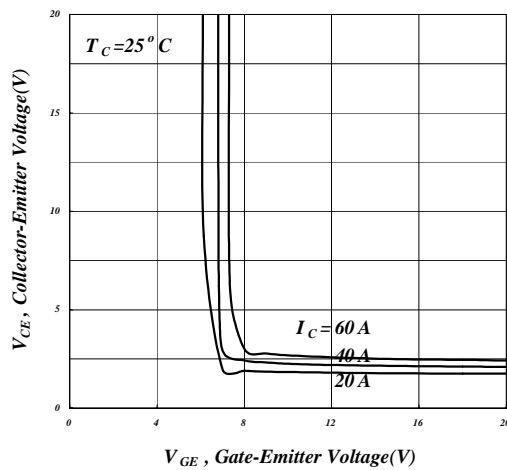


Fig 9. Saturation Voltage vs. V_GE

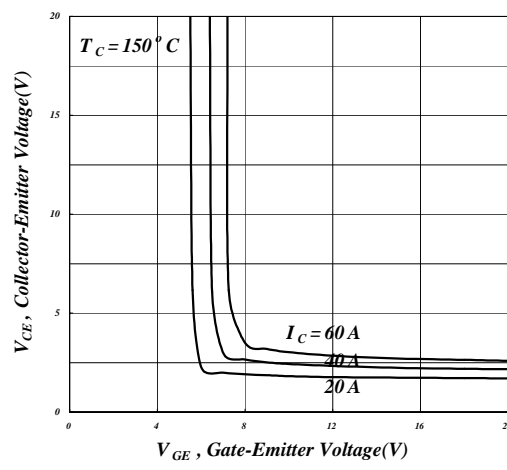


Fig 10. Saturation Voltage vs. V_GE

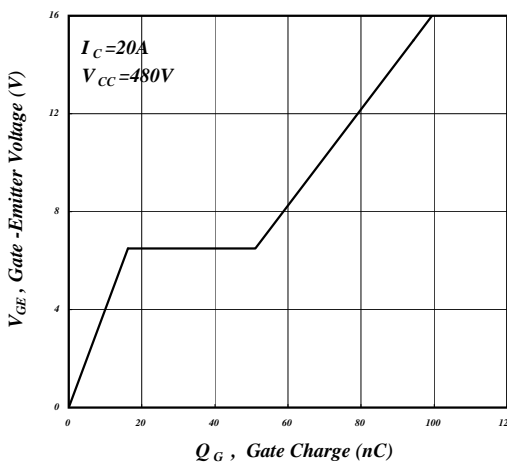


Fig 11. Gate Charge Characteristics

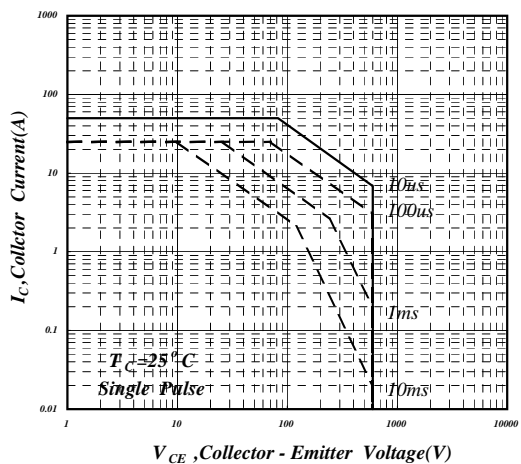


Fig 12. SOA Characteristics